

# DATA SHEET



## **PBSS3515VS**

15 V low  $V_{CEsat}$  PNP double  
transistor

Product specification  
Supersedes data of 2001 Sep 27

2001 Nov 07

# 15 V low $V_{CEsat}$ PNP double transistor

# PBSS3515VS

### FEATURES

- 300 mW total power dissipation
- Very small 1.6 x 1.2 mm ultra thin package
- Self alignment during soldering due to straight leads
- Low collector-emitter saturation voltage
- High current capability
- Improved thermal behaviour due to flat leads
- Replaces two SC75/SC89 packaged low  $V_{CEsat}$  transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and muting
- Low frequency driver circuits
- LCD backlighting
- Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

### DESCRIPTION

PNP low  $V_{CEsat}$  double transistor in a SOT666 plastic package.  
 NPN complement: PBSS2515VS.

### MARKING

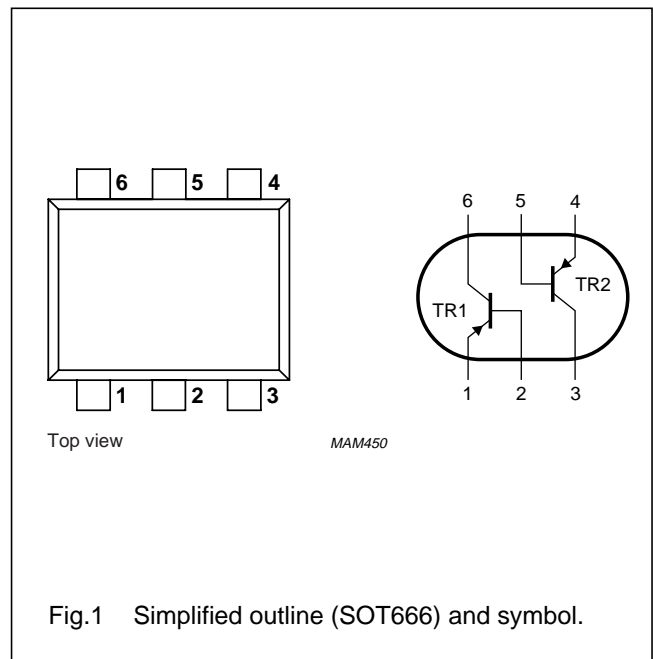
TYPE NUMBER	MARKING CODE
PBSS3515VS	35

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-15	V
$I_{CM}$	peak collector current	-1	A
$R_{CEsat}$	equivalent on-resistance	<500	m $\Omega$

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor unless otherwise specified</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	–15	V
$V_{CEO}$	collector-emitter voltage	open base	–	–15	V
$V_{EBO}$	emitter-base voltage	open collector	–	–6	V
$I_C$	collector current (DC)		–	–500	mA
$I_{CM}$	peak collector current		–	–1	A
$I_{BM}$	peak base current		–	–100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	200	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		65	+150	°C
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	300	mW

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

**Notes**

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering method is reflow soldering.

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**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

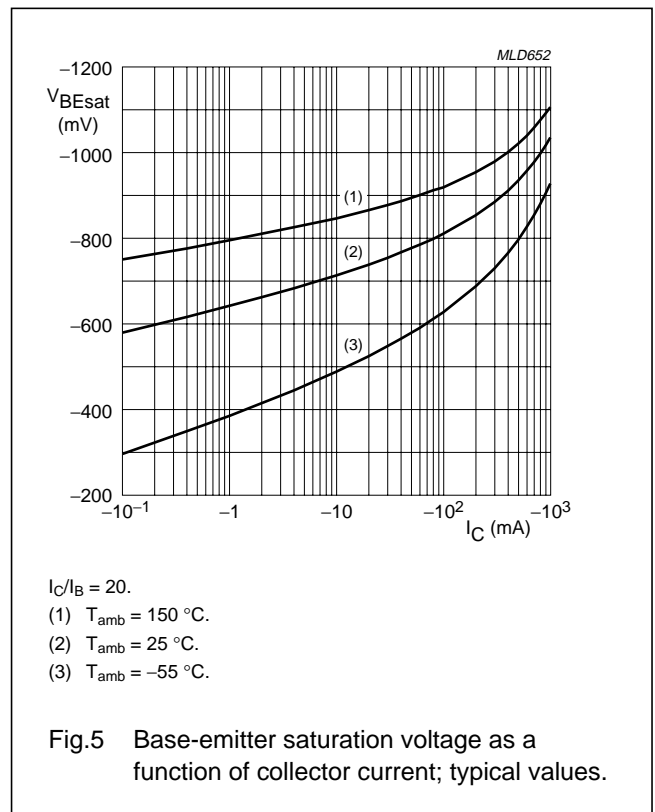
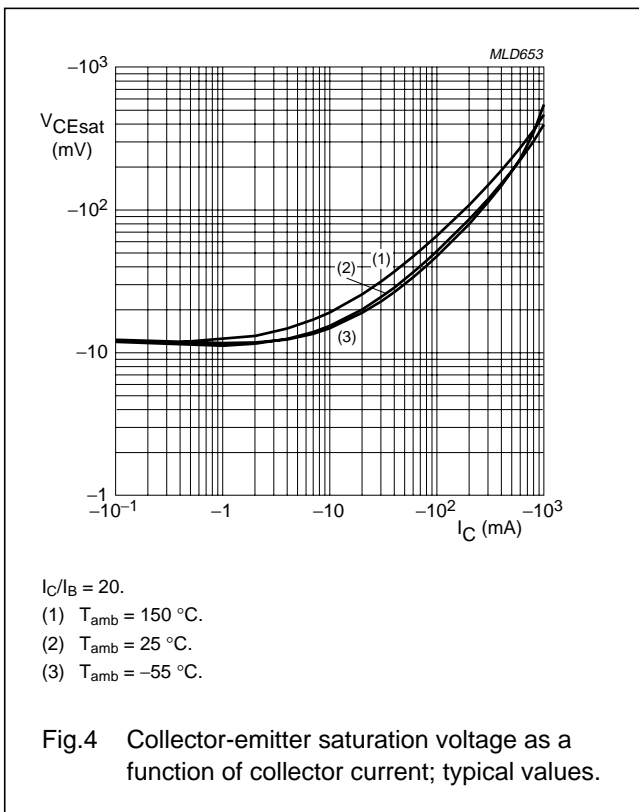
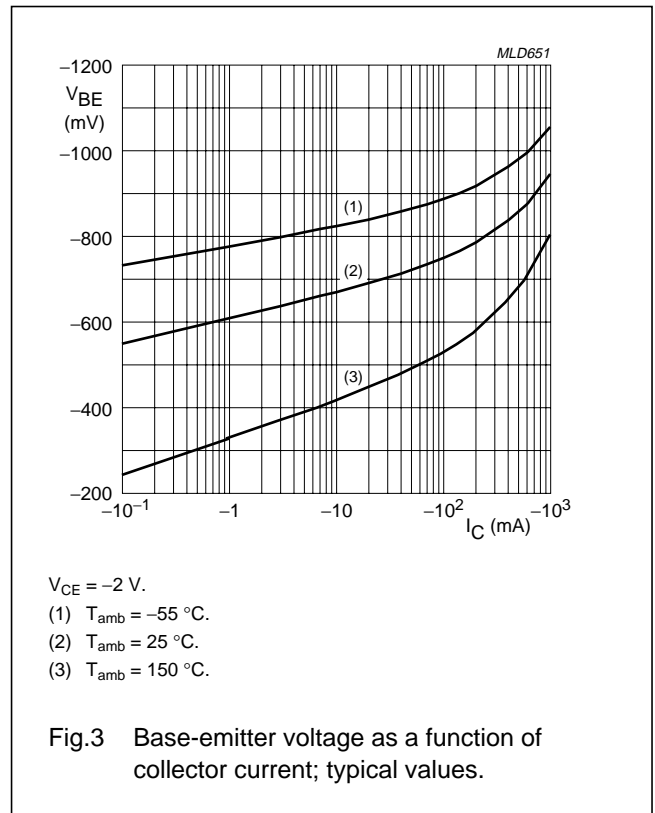
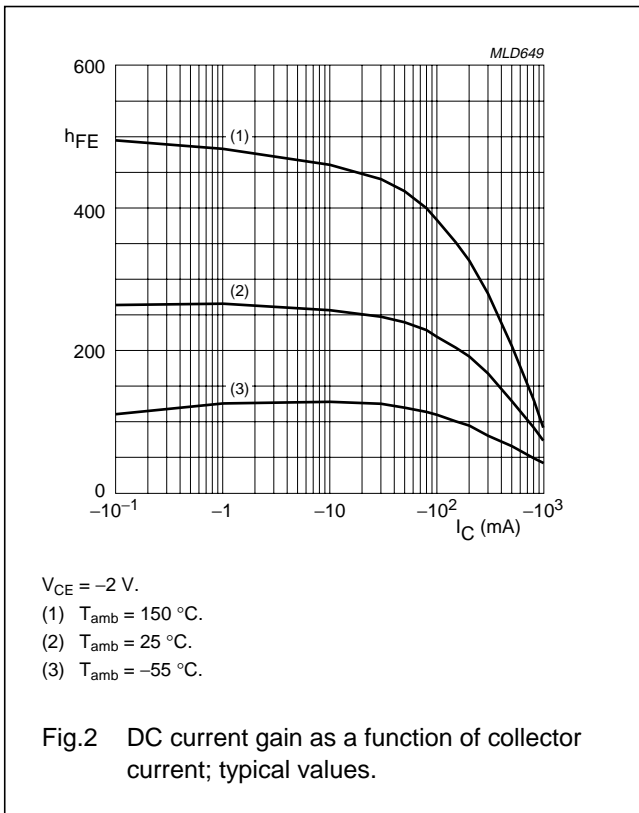
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per transistor unless otherwise specified</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -15\text{ V}; I_E = 0$	–	–	–100	nA
		$V_{CB} = -15\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–	–50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0$	–	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -2\text{ V}; I_C = -10\text{ mA}$	200	–	–	
		$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}; \text{note 1}$	150	–	–	
		$V_{CE} = -2\text{ V}; I_C = -500\text{ mA}; \text{note 1}$	90	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–	–25	mV
		$I_C = -200\text{ mA}; I_B = -10\text{ mA}$	–	–	–150	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	–	–250	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	300	<500	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	–	–1.1	V
$V_{BE}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}; \text{note 1}$	–	–	–0.9	V
$f_T$	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	280	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	10	pF

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

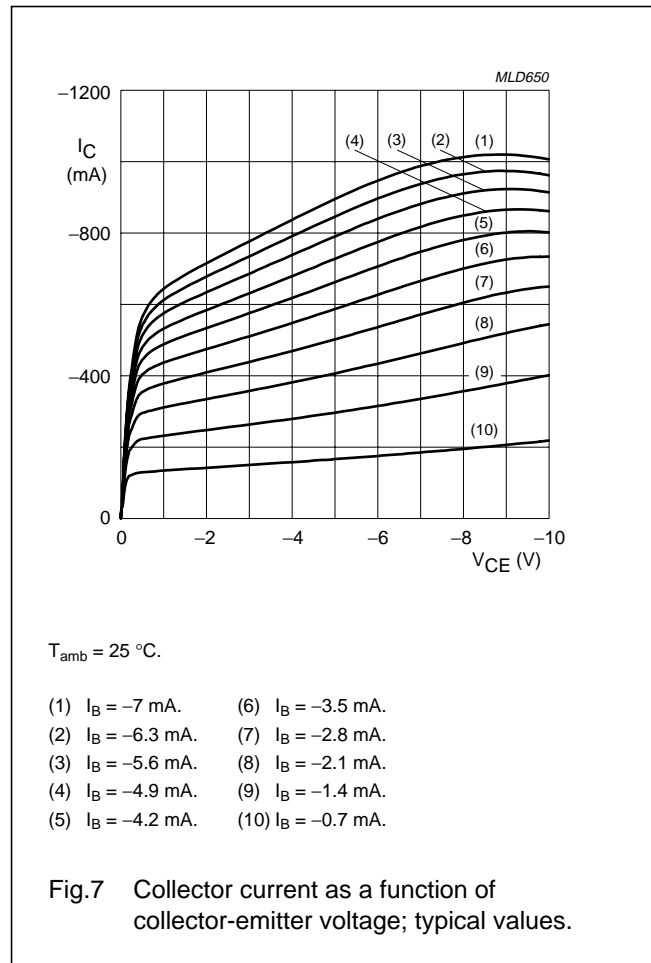
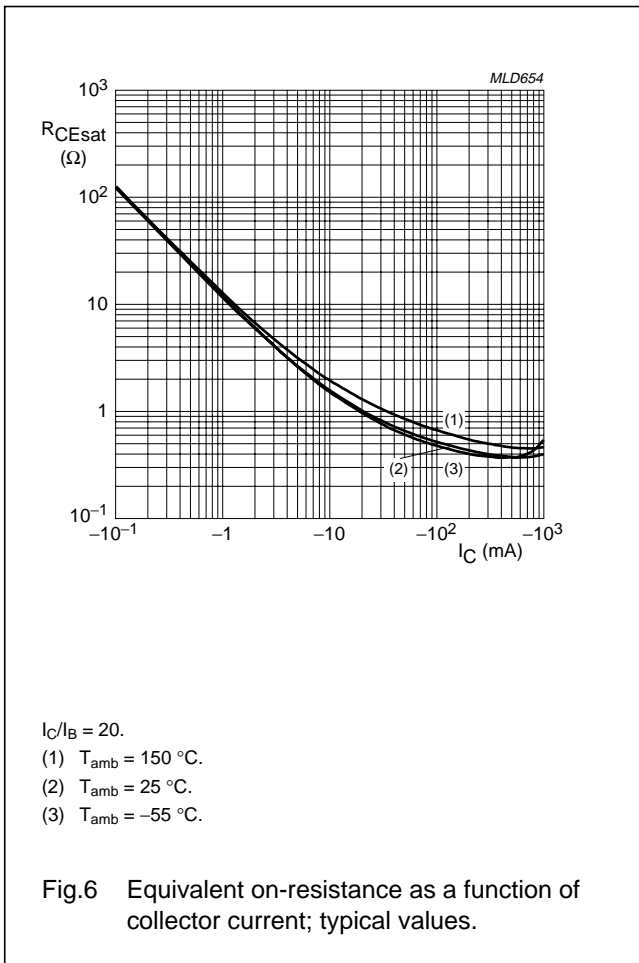
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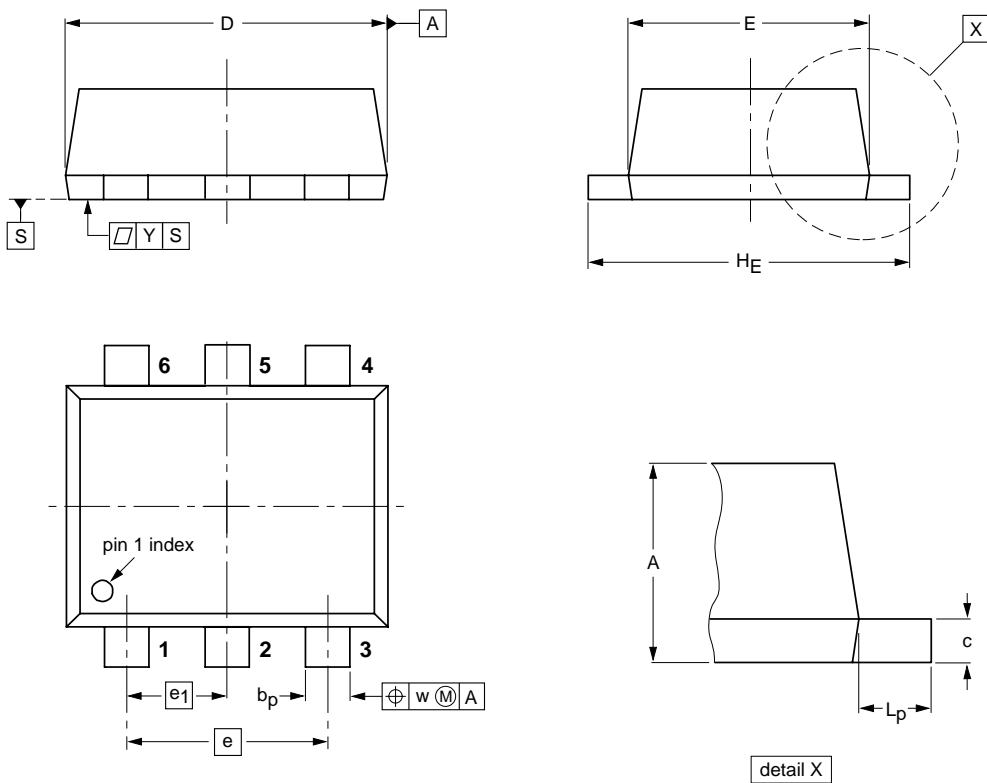
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

UNIT	A	$b_p$	c	D	E	e	$e_1$	$H_E$	$L_p$	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT666						01-01-04 01-08-27

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DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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**NOTES**

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**NOTES**

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